

500mA 40V(0.84x0.75mm)

Chip Information

Chip Size	0.84 x 0.75mm
Pad Size	0.71 x 0.62mm
Chip Quantity	17384 pcs/wafer
Scribe Line Width	50um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	40	V	
Average Forward Rectified Current	IF(AV)	500	mA	
Peak Forward Surge Current	IFSM	5.5	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.510	0.500	0.465	V	IF=500mA Ta=25degC
	VF2	0.460			V	IF=500mA Ta=100degC
	VF3	0.610			V	IF=1000mA Ta=25degC
	VF4	0.600			V	IF=1000mA Ta=100degC
	VF5					V
Maximum DC Reverse Current	IR1	15	9	1.5	uA	VR=40V Ta=25degC
	IR2	5000			uA	VR=40V Ta=100degC
	IR3	5	3	1	uA	VR=25V Ta=25degC
	IR4				uA	
Reverse Breakdown Voltage	BV	42	45	60	V	IR=20uA
Junction Capacitance	Cj	170			pF	VR=0V,f=1MHz
Reverse Recovery Time	trr				nS	

Ordering Information

Chip Type	Chip Thickness	Back Metal
XJC125	180 +/- 20um	Au(For Eutectic)
XJC127	150 +/- 20um	Au(For Eutectic)
XJC126	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:
Designed For MBR0540